

Title (en)
POLYCRYSTALLINE SILICON DEPOSITION METHOD

Title (de)
VERFAHREN ZUR ABSCHIEDUNG VON POLYKRISTALLINEM SILICIUM

Title (fr)
PROCÉDÉ SERVANT À DÉPOSER DU SILICIUM POLYCRISTALLIN

Publication
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Application
EP 14706635 A 20140226

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Abstract (en)
[origin: CA2898159A1] The subject matter of the invention is a polycrystalline silicon deposition method carried out in a reactor delimited laterally and at the top by a reactor wall and at the bottom by a bottom plate, slim rods being arranged on the bottom plate and heated, a silicon-containing gaseous reaction mixture being introduced into the reactor chamber through gas inlets in the reactor wall and in the bottom plate, and silicon being deposited on the slim rods. The method according to the invention is characterised in that the silicon-containing gaseous reaction mixture is introduced through gas inlets in the reactor wall at an angle of 0-45° to the lateral reactor wall.

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